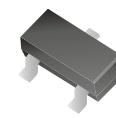
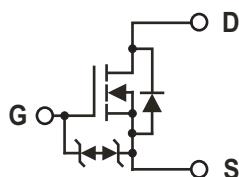


2N7002K-HF

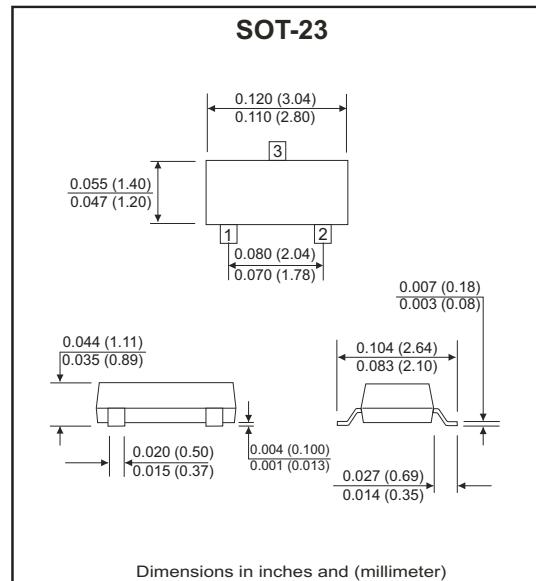
N-Channel
RoHS Device
Halogen Free

**Features**

- Small Signal MOSFET.
- ESD protected: 1000V.

Marking: 702**Equivalent Circuit**

G : Gate
 S : Source
 D : Drain

**Maximum Ratings** (at $T_A=25^\circ\text{C}$ unless otherwise noted)

Rating	Symbol	Value	Unit
Drain-Source voltage	V_{DSS}	60	Vdc
Drain-Gate Voltage ($R_{GS}=1.0 \text{ M}\Omega$)	V_{DGR}	60	Vdc
Drain current	I_D @ Continuous $T_c=25^\circ\text{C}$ (Note 1)	± 115	mAdc
	I_D @ Continuous $T_c=100^\circ\text{C}$ (Note 1)	± 75	
	I_{DM} @ Pulsed (Note 2)	± 800	
Gate-Source voltage	V_{GS} @ Continuous	± 20	Vdc
	V_{GSM} @ Non-repetitive ($t_p \leq 50\mu\text{s}$)	± 40	Vpk

Thermal Characteristics

Characteristics	Symbol	Max. Value	Unit
Total Device Dissipation FR-5 Board (Note 3) @ $T_A = 25^\circ\text{C}$	P_D	225	mW
		1.8	$\text{mW}/^\circ\text{C}$
Thermal Resistance, Junction to Ambient	$R_{\Theta JA}$	556	$^\circ\text{C}/\text{W}$
Total Device Dissipation Alumina Substrate (Note 4) @ $T_A = 25^\circ\text{C}$	P_D	300	mW
		2.4	$\text{mW}/^\circ\text{C}$
Thermal Resistance, Junction to Ambient	$R_{\Theta JA}$	417	$^\circ\text{C}/\text{W}$
Junction and Storage Temperature	T_J, T_{STG}	-55 to +150	$^\circ\text{C}$

- Note: 1. The Power Dissipation of the package may result in a lower continuous drain current.
 2. Pulse Test: Pulse Width $\leq 300\mu\text{s}$, Duty Cycle $\leq 2.0\%$.
 3. FR-5 = $1.0 \times 0.75 \times 0.062$ in.
 4. Alumina = $0.4 \times 0.3 \times 0.025$ in 99.5% alumina.

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REV: A

Electrical Characteristics (at $T_A=25^\circ\text{C}$ unless otherwise noted)

Characteristics	Conditions	Symbol	Min.	Typ.	Max.	Unit
Drain-Source Breakdown Voltage	$V_{GS}=0\text{V}$, $I_D=10\mu\text{A}$	$V_{(BR)DSS}$	60			V
Zero Gate Voltage Drain Current ($V_{GS}=0\text{V}$, $V_{DS}=60\text{V}$)	$T_J=25^\circ\text{C}$	I_{DSS}			1.0	μA
	$T_J=125^\circ\text{C}$				500	
Gate-Body Leakage Current, Forward	$V_{GS}=20\text{V}$	I_{GSSF}			1	μA
Gate-Body Leakage Current, Reverse	$V_{GS}=-20\text{V}$	I_{GSSR}			-1	μA

ON CHARACTERISTICS (Note 1)

Gate Threshold Voltage	$V_{DS}=V_{GS}$, $I_D=250\mu\text{A}$	$V_{GS(\text{th})}$	1	1.5	2.5	V
On-State Drain Current	$V_{DS}\geq 2.0\text{V}_{DS(\text{ON})}$, $V_{GS}=10\text{V}$	$I_{D(\text{ON})}$	500			mA
Static Drain-Source On-State Voltage	$V_{GS}=10\text{V}$, $I_D=500\text{mA}$	$V_{DS(\text{ON})}$			3.75	V
	$V_{GS}=5\text{V}$, $I_D=50\text{mA}$				0.375	
Static Drain-Source On-State Resistance	$V_{GS}=10\text{V}$, $I_D=500\text{mA}$ @ $T_c=25^\circ\text{C}$	$R_{DS(\text{ON})}$		1.4	7.5	Ω
	$V_{GS}=10\text{V}$, $I_D=500\text{mA}$ @ $T_c=125^\circ\text{C}$				13.5	
	$V_{GS}=5\text{V}$, $I_D=50\text{mA}$ @ $T_c=25^\circ\text{C}$			1.8	7.5	
	$V_{GS}=5\text{V}$, $I_D=50\text{mA}$ @ $T_c=125^\circ\text{C}$				13.5	
Forward Transconductance	$V_{DS}\geq 2.0\text{V}_{DS(\text{ON})}$, $I_D=200\text{mA}$	g_{fs}	80			mS

DYNAMIC CHARACTERISTICS

Input Capacitance	$V_{DS}=25\text{V}$, $V_{GS}=0\text{V}$, $f=1.0\text{MHz}$	C_{iss}		17	50	pF
Output Capacitance		C_{oss}		10	25	
Reverse Transfer Capacitance		C_{rss}		2.5	5.0	

SWITCHING CHARACTERISTICS (Note 1)

Turn-On Delay Time	$V_{DD}=25\text{V}$, $I_D=500\text{mA}$, $R_G=25\Omega$, $R_L=50\Omega$, $V_{GEN}=10\text{V}$	$t_{d(on)}$		7	20	nS
Turn-Off Delay Time		$t_{d(off)}$		11	40	

BODY-DRAIN DIODE RATINGS

Diode Forward On-Voltage	$I_S=115\text{mA}$, $V_{GS}=0\text{V}$	V_{SD}			-1.5	V
Source Current Continuous	Body Diode	I_S			-115	mA
Source Current Pulsed		I_{SM}			-800	mA

Note: 1. Pulse Test: Pulse Width $\leq 300\mu\text{s}$, Duty Cycle $\leq 2.0\%$.

RATING AND CHARACTERISTIC CURVES (2N7002K-HF)

Fig.1 Ohmic Region

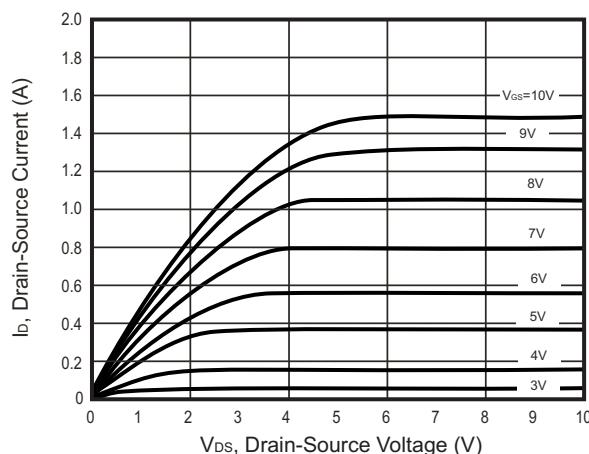


Fig.2 Transfer Characteristics

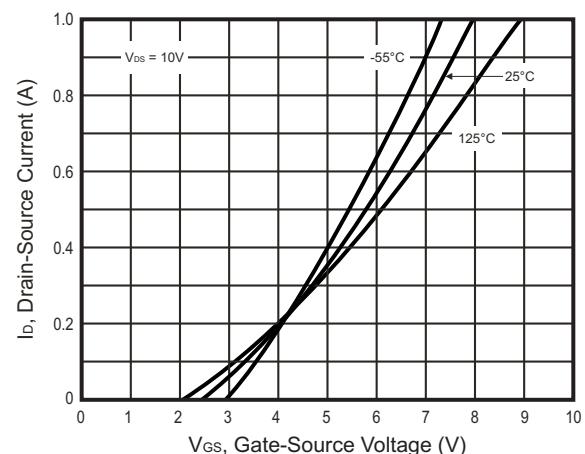


Fig.3 Temperature Versus Static Drain-Source On-Resistance

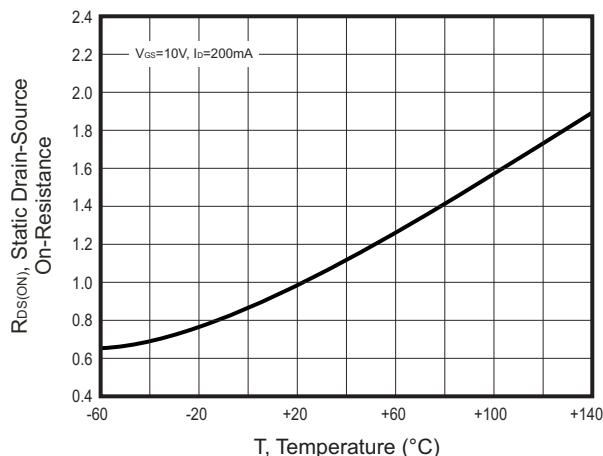
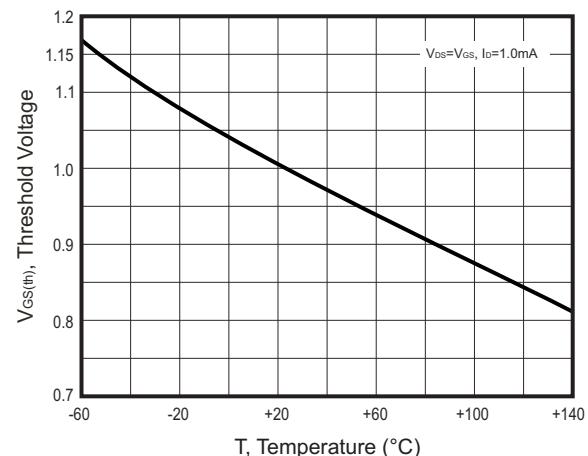


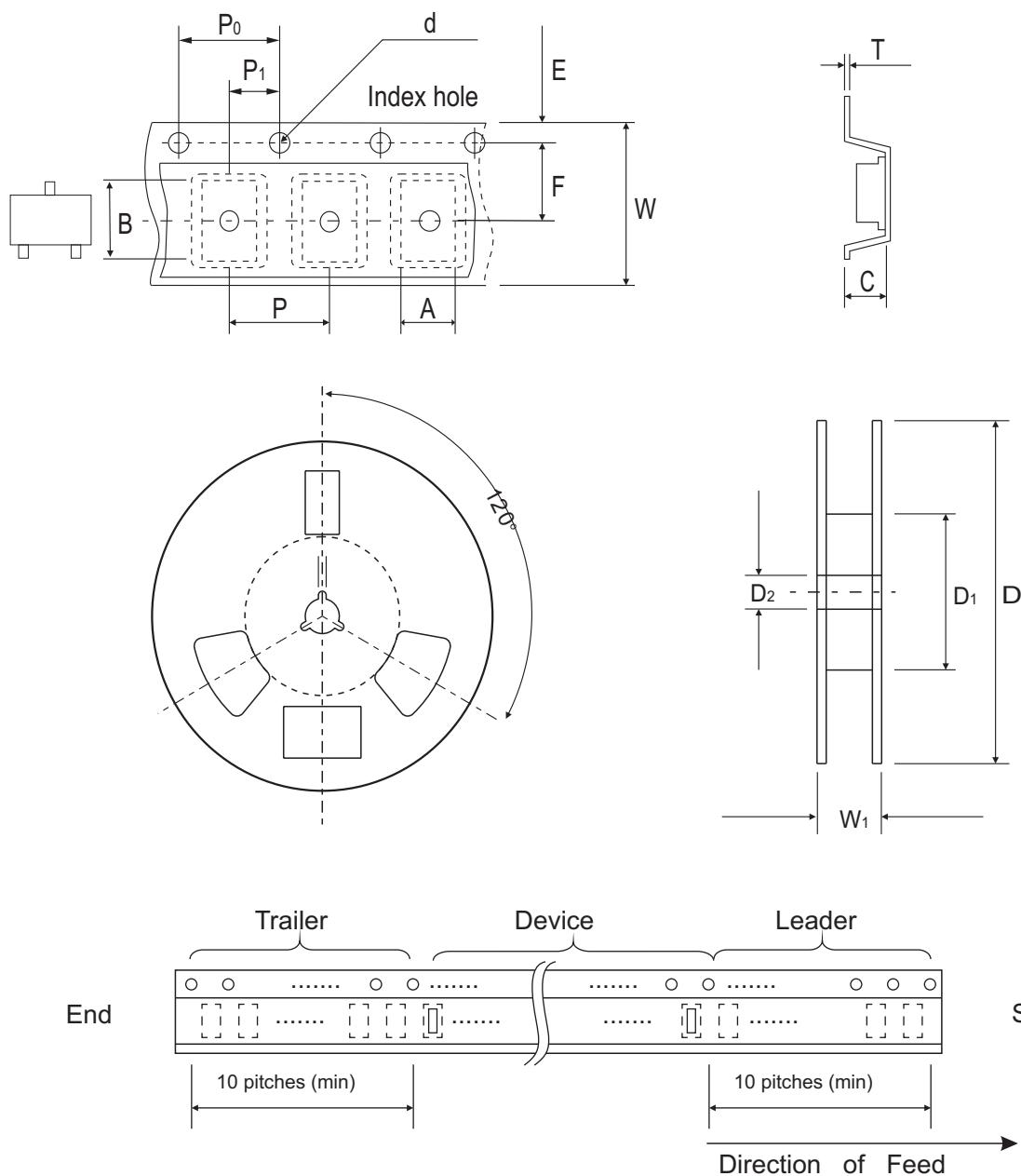
Fig.4 Temperature Versus Gate Threshold Voltage



$V_{GS} = 5V, I_D = 0.05A$

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Reel Taping Specification



SOT-23	SYMBOL	A	B	C	d	D	D ₁	D ₂
	(mm)	3.10 ± 0.10	2.85 ± 0.10	1.40 ± 0.10	1.55 ± 0.10	178 ± 1	50.0 MIN.	13.0 ± 0.20
	(inch)	0.122 ± 0.004	0.112 ± 0.004	0.055 ± 0.004	0.061 ± 0.004	7.008 ± 0.04	1.969 MIN.	0.512 ± 0.008

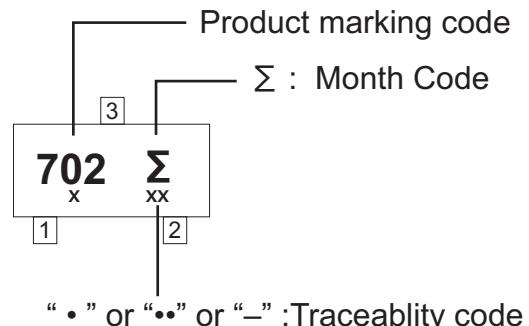
SOT-23	SYMBOL	E	F	P	P ₀	P ₁	W	W ₁
	(mm)	1.75 ± 0.10	3.50 ± 0.05	4.00 ± 0.10	4.00 ± 0.10	2.00 ± 0.05	8.00 ± 0.30	14.4 MAX.
	(inch)	0.069 ± 0.004	0.138 ± 0.002	0.157 ± 0.004	0.157 ± 0.004	0.079 ± 0.004	0.315 ± 0.008	0.567 MAX.

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REV: A

Marking Code

Part Number	Marking Code
2N7002K-HF	702 Σ



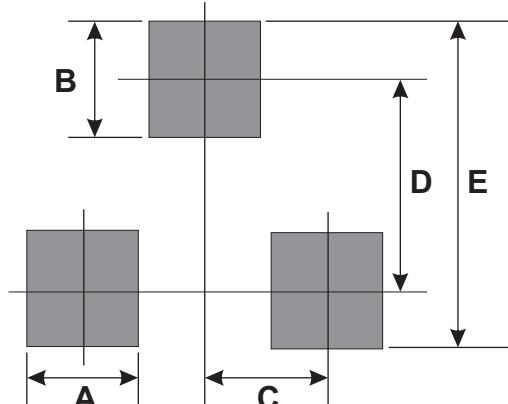
Month Code:

Month	Odd Year (per A.D.)	Even Year (per A.D.)
Jan	1	E
Feb	2	F
Wer	3	H
Apr	4	J
May	5	K
Jun	6	L

Month	Odd Year (per A.D.)	Even Year (per A.D.)
Jul	7	N
Aug	8	P
Sep	9	U
Oct	T	X
Nov	V	Y
Dec	C	Z

Suggested PAD Layout

SIZE	SOT-23	
	(mm)	(inch)
A	0.80	0.031
B	0.90	0.035
C	0.95	0.037
D	2.00	0.079
E	2.90	0.114



Standard Packaging

Case Type	REEL PACK	
	REEL (pcs)	Reel Size (inch)
SOT-23	3,000	7

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